

FORMING A HIGH DIELECTRIC
CONSTANT FILM USING METALLIC PRECURSOR

Abstract of the Disclosure

A liquid form oxidizer may be utilized to form a high dielectric constant dielectric material from a metallic precursor for semiconductor applications. The use of a
5 liquid rather than a gaseous oxidizer reduces the presence of an oxidation under layer under the metallic precursor. It may also, in some embodiments, result in a purer dielectric film.